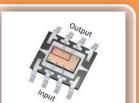
## Infineon gate driver IC technologies and applications



#### **Level-shifting**

## junction isolation (JI)

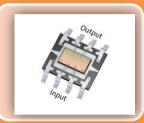
- Industry standard gate drivers using rugged proprietary HVIC process
- Tailored for specific motor- control and switch-mode power applications silicon-on-insulator (SOI)
- New high-voltage technology with inherent integrated boot-strap diode capability and industry best-in-class robustness against negative VS transient spikes
- Higher level of integration reduces OM and total system cost



## **Galvanic** isolation technology

## **Coreless transformer (CT)**

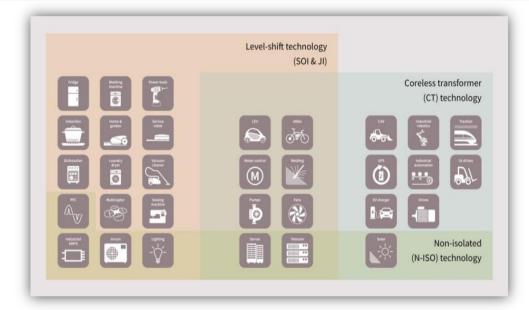
- Magnetically-coupled isolation technology provides galvanic isolation for industrial applications
- Flexible configurations and options for output current (up to 10 A), DESAT protection, active Miller clamp isolation rating, and packages



## Non-isolated (N-ISO)

- Single- and dual-low-side drivers with flexible options for output current, logic configurations, UVLO, and packages
- •Rugged technology of the high-voltage gate drivers, and on the latest state-of-the-art 0.13-µm process

The industrial and general purpose gate driver ICs are well suited for many applications, such as industrial, EV Charging and battery driven applications:



## Industrial

#### Inverter (<5 kW):

## 6EDL04N06PT

- Thin-film-SOI-technology
- Ultra-fast bootstrap diodes
- Shutdown of all switches during error conditions

### Inverter (<30 kW):

#### 1ED020I12-F2

- Galvanically isolated coreless transformer driver
- Desaturation protection
- Active miller clamp

## PFC: SMPS:

#### PFC; SIMPS: <u>2EDN8524F</u>

- Dual-channel low-side
- 5 A source / 5 A sink
- High system level efficiencies, excellent power density and consistent system robustness

## **EV Charging**

#### DC-DC: 1EDC20I12AH

#### HB (LLC): 1EDC60I12AH

- 7.6 mm creepage clearance
  UL 1577 certified with V<sub>ISO</sub> = 2500 V<sub>(rms)</sub>
  for 1 min
- Separate source and sink outputs
- Short circuit clamping
- Active shutdown

#### PFC:

## <u>IR4427S</u>

- Gate drive supply range from 6 to 20 V
- Matched propagation delay for both channels

## 2EDN7524F

- Dual-channel low-side
- 5 A source / 5 A sink
- High system level efficiencies, excellent power density and consistent system robustness

# Battery driven applications

# Drone, e-bike, e-scooter, vacuum, service robotic:

#### IRS2008S

- 70 ns/35 ns typical turn-on rise/turn-off fall times
- Less than 60 ns delay matching time
- 520 ns deadtime and cross-conduction prevention logic

### 6EDL04N02PR

- Separate control circuits for all six drives; Interlock
- Ultra-fast integrated bootstrap diode (RBSD 40 Ω)
- Over-current protection
- Shutdown of all switches during error conditions
- Evaluation board available: EVAL-6EDL04N02PR

#### IR2011S

- Independent low and high side channels
- Matched propagation delay for both channels